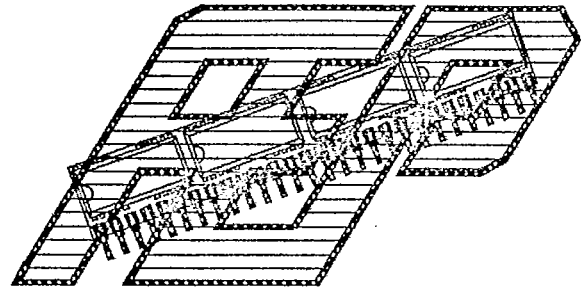


T-46-23-18

- >> 1,048,576 x 8 Organization
- >> Low 0.510 inch stand-off height (0.350 using 90 degree lead pins)
- >> 28 pin SIP is shorter in length than standard modules
- >> Single +5V power supply
- >> TTL compatible



**1 MEGAWORD BY 8 BIT LOW
PROFILE DYNAMIC RAM MODULE**

DESCRIPTION:

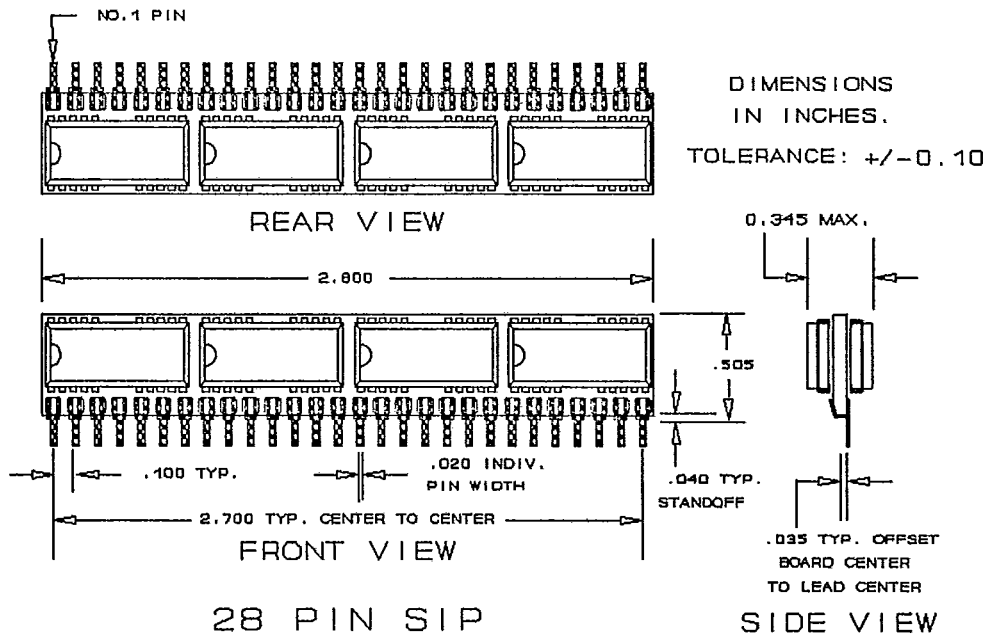
The AEPDX1M8LB is a low profile 1 megaword by 8 bit dynamic random access memory module in a 28 pin single in-line package format. Physically it consists of an FR4 PC material substrate mounted with eight 1M x 1 SOJ (small outline J-leaded package) ICs, eight 0.18 microfarad capacitors, and 28 edge clip I/O pins.

The module can use any of the 1M x 1 SOJs available from multiple manufacturers in both NMOS and low power CMOS technologies and with a variety of access speeds.

Power dissipation is also determined by the ICs used but is typically 50 milliwatts in standby and 2.5 to 3.5 watts when active (ratings for the CMOS version). A single 5V power supply is required.

Two I/O pin configurations are available: the standard vertical for mounting the module upright and the horizontal version using 90 degree lead pins. This lays the module over on it's side consuming slightly more board space but fitting in a low 0.350 inch of above board clearance.

**SPECIFICATION DRAWING
1Mx8 LOW PROFILE DRAM MODULE**



NOTE: .18MF CAPACITORS IN 8 PLACES UNDERNEATH DEVICES MVL



1 MEGAWORD x 8 LOW PROFILE DYNAMIC RAM MODULE

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SIP PIN-OUT CONFIGURATION

FUNCTIONAL DIAGRAM

- 1 — VCC
- 2 — CAS*
- 3 — DQ₁
- 4 — A₀
- 5 — A₁
- 6 — DQ₂
- 7 — A₂
- 8 — A₃
- 9 — VSS
- 10 — DQ₃
- 11 — A₄
- 12 — A₅
- 13 — DQ₄
- 14 — A₆
- 15 — A₇
- 16 — DQ₅
- 17 — A₈
- 18 — A₉
- 19 — ANC**
- 20 — DQ₆
- 21 — WE*
- 22 — VSS
- 23 — DQ₇
- 24 — NC
- 25 — DQ₈
- 26 — NC
- 27 — RAS*
- 28 — VCC

* ACTIVE WHEN LOW

** ANC FOR NEXT
GENERATION 4Mx8 SRAM

